



N-Channel 100-V (D-S) 200°C MOSFET

PRODUCT SUMMARY

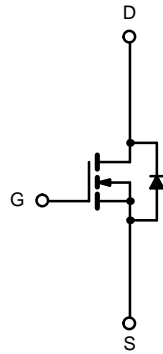
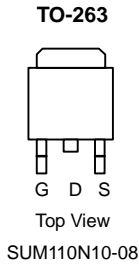
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
100	0.0085 @ $V_{GS} = 10$ V	110 ^a

FEATURES

- TrenchFET® Power MOSFETS
- 200°C Junction Temperature
- New Package with Low Thermal Resistance

APPLICATIONS

- Automotive
 - 42-V Power Bus
 - DC/DC Conversion
 - Motor Drivers
 - Injection Systems



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 200^\circ\text{C}$)	I_D	$T_C = 25^\circ\text{C}$	110 ^a
		$T_C = 125^\circ\text{C}$	75
Pulsed Drain Current	I_{DM}	440	A
Avalanche Current	I_{AR}	75	
Repetitive Avalanche Energy ^b	E_{AR}	280	mJ
Maximum Power Dissipation ^b	P_D	$T_C = 25^\circ\text{C}$	437.5 ^c
		$T_A = 25^\circ\text{C}^d$	3.75
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 200	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) ^d	R_{thJA}	40	$^\circ\text{C/W}$
Junction-to-Case (Drain)	R_{thJC}	0.4	

Notes

- Package limited.
- Duty cycle $\leq 1\%$.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{DS} = 0 V, I _D = 250 μA	100			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2		4	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V			1	μA
		V _{DS} = 80 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 80 V, V _{GS} = 0 V, T _J = 200 °C			10	mA
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	120			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 30 A		0.0068	0.0085	Ω
		V _{GS} = 10 V, I _D = 30 A, T _J = 125 °C			0.016	
		V _{GS} = 10 V, I _D = 30 A, T _J = 200 °C			0.025	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 30 A	25			S
Dynamic^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		8700		pF
Output Capacitance	C _{oss}			740		
Reverse Transfer Capacitance	C _{rss}			450		
Total Gate Charge ^c	Q _g	V _{DS} = 50 V, V _{GS} = 10 V, I _D = 85 A		140	160210	nC
Gate-Source Charge ^c	Q _{gs}			41		
Gate-Drain Charge ^c	Q _{gd}			41		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 50 V, R _L = 0.6 Ω I _D ≅ 85 A, V _{GEN} = 10 V, R _G = 2.5 Ω		20	30	ns
Rise Time ^c	t _r			110	170	
Turn-Off Delay Time ^c	t _{d(off)}			65	100	
Fall Time ^c	t _f			100	150	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)^b						
Continuous Current	I _S				110	A
Pulsed Current	I _{SM}				240	
Forward Voltage ^a	V _{SD}	I _F = 50 A, V _{GS} = 0 V		1.0	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 50 A, di/dt = 100 A/μs		70	140	ns
Peak Reverse Recovery Current	I _{RM(REC)}			5.5	10	A
Reverse Recovery Charge	Q _{rr}			0.19	0.35	μC

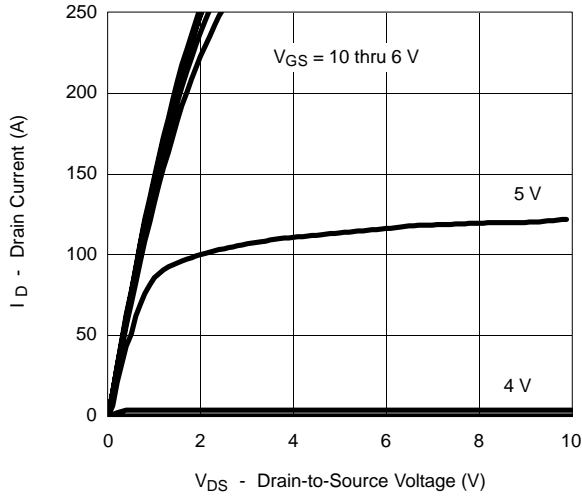
Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

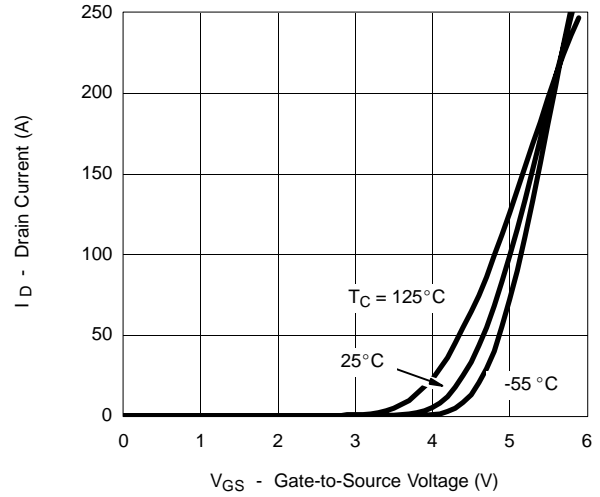


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

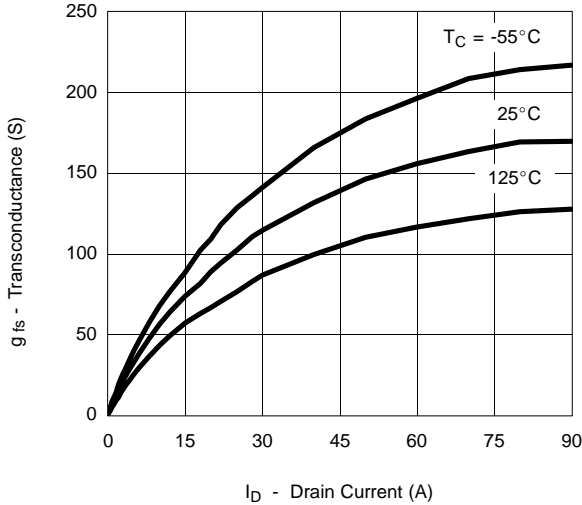
Output Characteristics



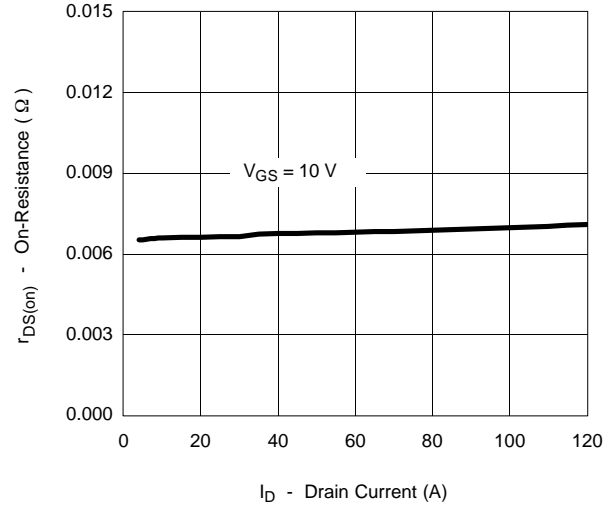
Transfer Characteristics



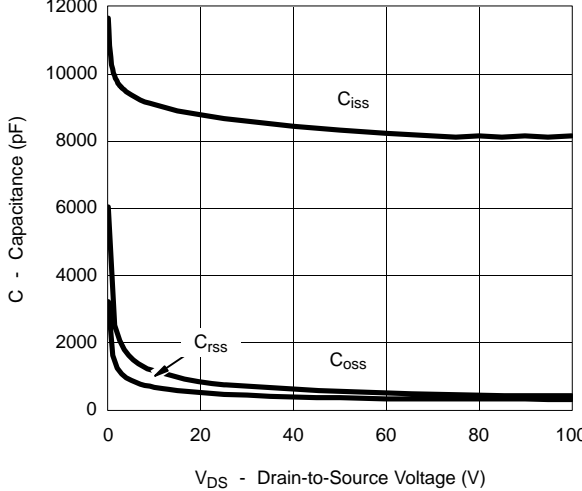
Transconductance



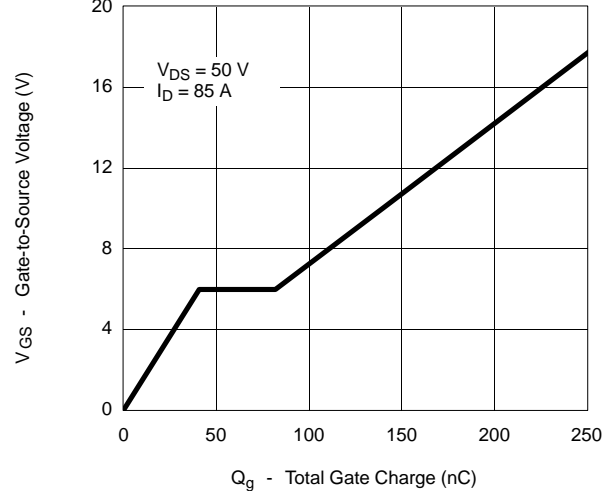
On-Resistance vs. Drain Current



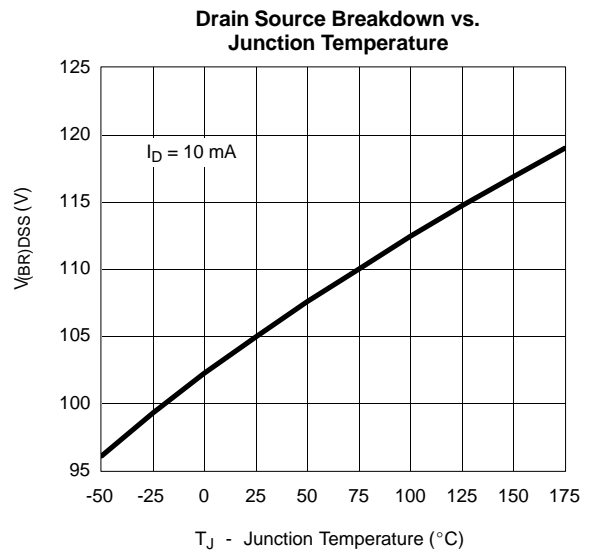
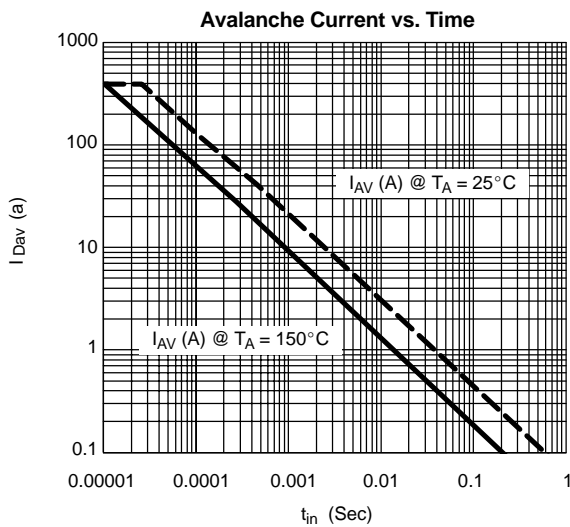
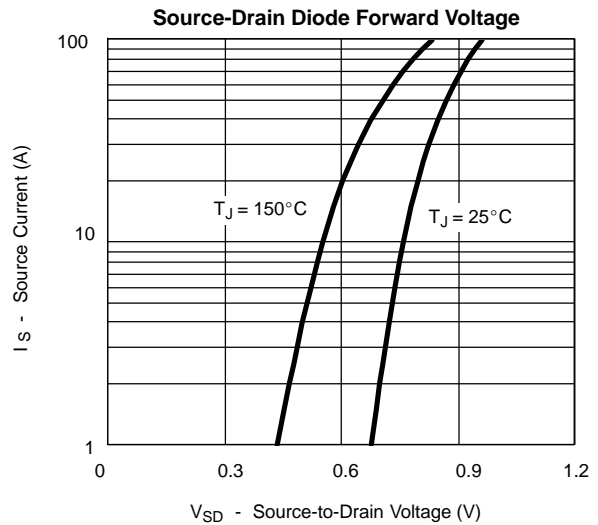
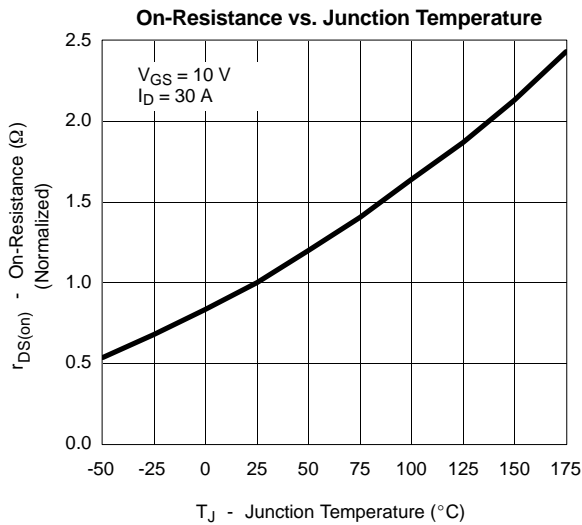
Capacitance



Gate Charge



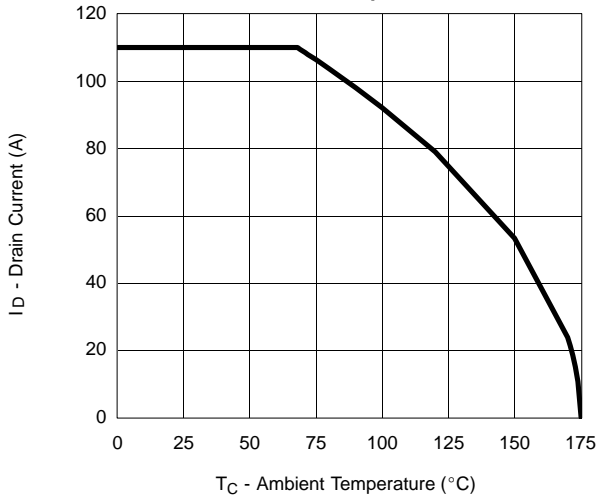
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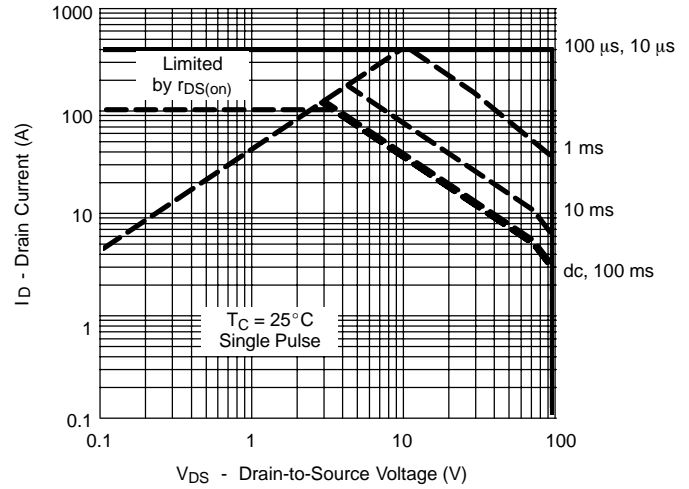


THERMAL RATINGS

Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

